

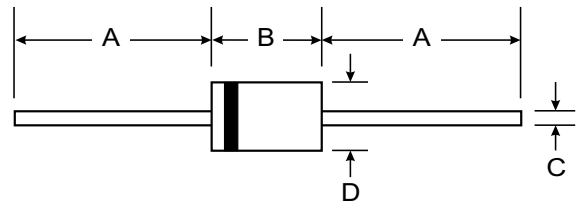
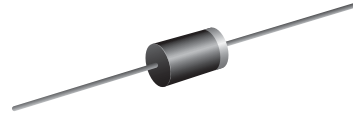
**VOLTAGE RANGE: 40 - 100V**  
**CURRENT: 2.0 A**

### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

### Mechanical Data

- Case: DO-15, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-15		
Dim	Min	Max
A	25.40	—
B	5.50	7.62
C	0.686	0.889
D	2.60	3.60
All Dimensions in mm		

### Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	21DQ04	21DQ06	21DQ10	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>VRM</sub> V <sub>R</sub>	40	60	100	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	42	70	V
Average Rectified Output Current @T <sub>L</sub> = 100°C (Note 1)	I <sub>o</sub>	2.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	50			A
Forward Voltage @I <sub>F</sub> = 2.0A	V <sub>FM</sub>	0.55	0.70	0.85	V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	I <sub>RM</sub>	0.5 10			mA
Typical Junction Capacitance (Note 2)	C <sub>j</sub>	170	140		pF
Typical Thermal Resistance (Note 1)	R <sub>θJA</sub>	35			°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150			°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.  
 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

## RATINGS AND CHARACTERISTIC CURVES 21DQ04 THRU 21DQ10

